

MMBTA28



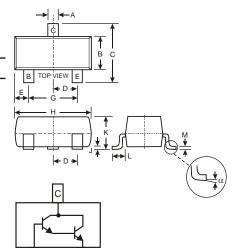
NPN SURFACE MOUNT DARLINGTON TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- High Current Gain
- Lead Free/RoHS Compliant (Note 3)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking (See Page 3): K6R
- Ordering & Date Code Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23									
Dim	Min	Max							
Α	0.37	0.51							
В	1.20	1.40							
С	2.30	2.50							
D	0.89	1.03							
Е	0.45	0.60							
G	1.78	2.05							
Н	2.80	3.00							
J	0.013	0.10							
K	0.903	1.10							
L	0.45	0.61							
М	0.085	0.180							
	0°	8°							
All Dimensions in mm									

Maximum Ratings @ T_A = 25°C unless otherwise specified

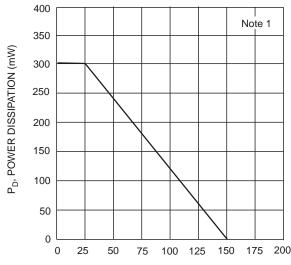
Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	80	V	
Collector-Emitter Voltage	V _{CEO}	80	V	
Emitter-Base Voltage	V _{EBO}	12	V	
Collector Current - Continuous	I _C	500	mA	
Power Dissipation (Note 1)	Pd	300	mW	
Thermal Resistance, Junction to Ambient (Note 1)	R JA	417	°C/W	
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C	

Electrical Characteristics @ TA = 25°C unless otherwise specified

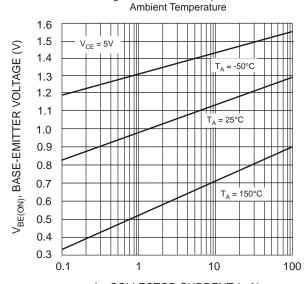
Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 2)							
Collector-Base Breakdown Voltage	-Base Breakdown Voltage V _{(BR)CBO} 80				$I_C = 100 \mu A I_E = 0$		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	12		V	$I_E = 100 \mu A I_C = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	80		V	I _C = 100μA I _B = 0		
Callactor Cutoff Current			100	nA	V _{CB} = 60V, I _E = 0		
Collector Cutoff Current	I _{CES}		500	nA	V _{CE} = 10V		
Emitter Cutoff Current	utoff Current I _{EBO} 100 n.						
ON CHARACTERISTICS (Note 2)							
DC Current Gain	h _{FE}	10,000 10,000			I _C = 10mA, V _{CE} = 5.0V I _C = 100mA, V _{CE} = 5.0V		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		1.5	V	I _C = 100mA, I _B = 100μA		
Base-Emitter Saturation Voltage	V _{BE(SAT)}		2.0		I _C = 100mA, V _{CE} = 5.0V		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C _{obo}	8.0 T	ypical	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0		
Input Capacitance	C _{ibo}	15 Typical 125		pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$		
Current Gain-Bandwidth Product	f⊤			MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz		

- Device mounted on FR-4 PCB, 1.6x1.6x0.06 inch pad layout as shown on Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
 - Short duration pulse test used to minimize self-heating effect.
 - 3. No purposefully added lead.

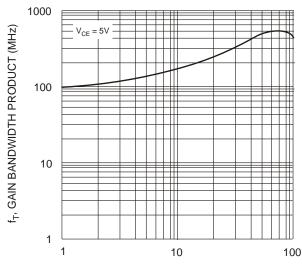




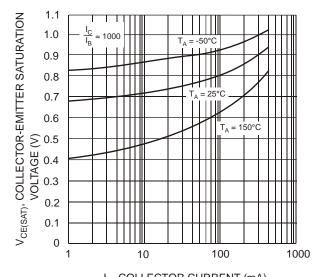
T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs



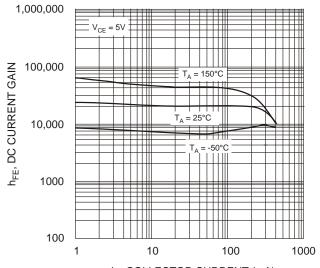
I_C, COLLECTOR CURRENT (mA) Fig. 3 Typical Base-Emitter Voltage vs. Collector Current



COLLECTOR CURRENT $I_{\rm C}$ (mA) Fig. 5 Typical Gain Bandwidth Product vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 2 Typical Collector-Emitter Saturation Voltage
vs. Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 4 Typical DC Current Gain vs. Collector Current

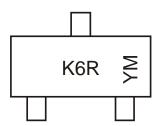


Ordering Information (Note 4)

Device	Packaging	Shipping
MMBTA28-7-F	SOT-23	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K6R = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	Т	U	V	W	Х	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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